Matter Coupling to Strong Electromagnetic Fields in Two-Level Quantum Systems with Broken Inversion Symmetry

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We demonstrate theoretically the parametric oscillator behavior of a two-level quantum system with broken inversion symmetry exposed to a strong electromagnetic field. A multitude of resonance frequencies and additional harmonics in the scattered light spectrum as well as altered Rabi frequency are predicted to be inherent to such systems. In particular, dipole radiation at the Rabi frequency appears to be possible. Since the Rabi frequency is controlled by the strength of coupling electromagnetic field, the effect can serve for the frequency-tuned parametric amplification and generation of electromagnetic waves. Manifestation of the effect is discussed for III-nitride quantum dots with strong build-in electric field breaking the inversion symmetry. Terahertz emission from arrays of such quantum dots is shown to be experimentally observable.

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The resonant interaction of quantum systems with strong electromagnetic field [1, 2, 3] is permanently in the focus of interest, both due to high methodological value of arising problems and their direct relation to current applied projects, such as new generation of highefficient lasers [3, 4, 5], laser cooling of atoms [2], development of basis for quantum information processing [6, 7], etc. One of bright manifestations of the strong field-matter coupling is the Rabi effect [2]: oscillations of the level population in a quantum system exposed to a monochromatic electromagnetic wave. The simplest physical model leading to harmonic Rabi oscillations is a two-level symmetrical quantum system placed in a given classical single-mode electromagnetic field [2]. Incorporation into this simplest model additional physical factors results in many nontrivial effects. For example, accounting for the quantum nature of light leads to the concept of radiation-dressed atoms [1] and the 'collapse-revivals' phenomenon in the population dynamics of a system exposed to coherent light. Time-domain modulation of the field-matter coupling constant [8, 9], local-field effects in nanostructures [10, 11] and phonon-induced dephasing [12, 13] provide new possibilities for the control of the Rabi oscillation dynamics. Many interesting effects manifest themselves in more complex systems, such as two coupled Rabi oscillators [14, 15] where Rabi effect is observed between ground state and two-electron entangled state, Rabi oscillators based on superconducting electrical circuits [6], and systems where Rabi oscillations are strongly influenced by intraband motion of quasiparticles [16]. In the given Letter we investigate the role in the Rabi effect of a new physical factor — violation of the inversion symmetry. Inherent in many quantum systems (particularly, in semiconductor nanostructures), the factor is meanwhile ignored by the conventional physical model [2] of Rabi oscillations.

Let us consider a two-level quantum system with $|a\rangle$ and $|b\rangle$ as excited and ground states, respectively. Let the system interacts with a classical linearly polarized monochromatic electromagnetic field. The system is described by the Hamiltonian $\hat{\mathcal{H}} = \hat{\mathcal{H}}_0 + \hat{\mathcal{H}}_{int}$. The freeparticle Hamiltonian, written in the basis of these two states, is $\mathcal{H}_0 = \hbar \omega_0 \hat{\sigma}_z / 2$, where $\hat{\sigma}_z$ is the Pauli matrix and ω_0 is the resonant frequency of the two-level system. The interaction Hamiltonian is expressed in terms of the amplitude **E** and frequency ω of the driving field by $\mathcal{H}_{int} = -\mathbf{Ed}\cos(\omega t)$, where **d** is the electric dipole moment operator and $\mathbf{d}_{ij} = \langle i|\hat{\mathbf{d}}|j\rangle$ are its matrix elements. As usual, we assume the nondiagonal matrix elements \mathbf{d}_{ab} to be real-valued and equal to each other, i.e. $\mathbf{d}_{ab} = \mathbf{d}_{ba}$. The critical assumption, which distinguishes the systems being considered from standard ones, is the violation of the inversion symmetry. As a result, diagonal matrix elements of the dipole moment operator prove to be nonequivalent, $\mathbf{d}_{aa} \neq \mathbf{d}_{bb}$, dictating thus physical effects described hereafter.

We shall seek the solution of the Schrödinger equation with the Hamiltonian described above in the form of $|\psi\rangle = C_a(t)|a\rangle + C_b(t)|b\rangle$. Substituting this expression into the Schrödinger equation, we arrive at the equations

$$i\hbar \dot{C}_a = \left[\frac{\hbar\omega_0}{2} - \mathbf{E}\mathbf{d}_{aa}\cos(\omega t)\right] C_a - \mathbf{E}\mathbf{d}_{ab}\cos(\omega t) C_b , \quad (1)$$

$$i\hbar\dot{C}_b = \left[-\frac{\hbar\omega_0}{2} - \mathbf{E}\mathbf{d}_{bb}\cos(\omega t)\right]C_b - \mathbf{E}\mathbf{d}_{ba}\cos(\omega t)C_a.(2)$$

In order to solve these equations with respect to C_a and C_b , we first rewrite them for modified amplitudes $c_{a,b} = C_{a,b} \exp[\pm i\omega_0 t/2 - i\phi_{a,b}(\omega,t)]$, where $\phi_j(\omega,t) = \mathbf{Ed}_{jj} \sin(\omega t)/\hbar\omega$, and signs \pm correspond to indexes a and b, respectively. The system of equations (1)–(2) is

then reduced to the form as follows

$$\hbar \dot{c}_a = i \mathbf{E}_{\text{eff}}^* \mathbf{d}_{ab} \cos(\omega t) c_b e^{i\omega_0 t} \,, \tag{3}$$

$$\hbar \dot{c}_b = i \mathbf{E}_{\text{eff}} \mathbf{d}_{ba} \cos(\omega t) c_a e^{-i\omega_0 t} \,, \tag{4}$$

where the effective electric field strength is

$$\mathbf{E}_{\text{eff}}(t) = \mathbf{E}e^{-i\kappa\sin(\omega t)} = \mathbf{E}\sum_{n=-\infty}^{\infty} J_n(\kappa)e^{in\omega t}, \quad (5)$$

 $J_n(\kappa)$ is the Bessel function of the first kind, and $\kappa = \mathbf{E}(\mathbf{d}_{bb} - \mathbf{d}_{aa})/\hbar\omega$ is the symmetry violation parameter. Let us stress that Eqs. (3)–(4) are analogous to standard equations of two-level system [2] with the only difference that the driving field amplitude E is replaced by the effective amplitude (5). That the effective amplitude $\mathbf{E}_{\text{eff}}(t)$ is time-dependent causes the system to become a parametric oscillator with full set of intrinsic properties, unusual for standard Rabi oscillators. In particular, a multitude of resonant frequencies $\omega = \omega_0/n$, n = 1, 2, 3, ... appears in the system. Further we shall assume that the driving field frequency ω is in the vicinity of the frequency ω_0/m (m-th resonance) and the conditions $|2\mathbf{E}\mathbf{d}_{ab}mJ_m(\kappa)/\kappa\hbar(\omega_0-m\omega)| \gtrsim 1$ and $|2\mathbf{E}\mathbf{d}_{ab}nJ_n(\kappa)/\kappa\hbar\omega|\ll 1\ (n=1,2,3,...)$ are fulfilled, allowing us to neglect interaction of the two-level system with all harmonics (5) other than harmonics $m \pm 1$. Then the system of equations (3)–(4) resumes the form analogous to equations for symmetric two-level systems and can easily be solved by invoking the rotating-wave approximation [2]. As a result, we obtain

$$C_{a}(t) = \left\{ C_{a}(0) \left[\cos\left(\frac{\Omega t}{2}\right) - \frac{i\Delta}{\Omega} \sin\left(\frac{\Omega t}{2}\right) \right] + i\frac{\Omega_{R}}{\Omega} C_{b}(0) \sin\left(\frac{\Omega t}{2}\right) \right\} e^{-im\omega t/2} e^{i\phi_{a}(\omega,t)}, \quad (6)$$

$$C_{b}(t) = \left\{ C_{b}(0) \left[\cos\left(\frac{\Omega t}{2}\right) + \frac{i\Delta}{\Omega} \sin\left(\frac{\Omega t}{2}\right) \right] + i\frac{\Omega_{R}}{\Omega} C_{a}(0) \sin\left(\frac{\Omega t}{2}\right) \right\} e^{im\omega t/2} e^{i\phi_{b}(\omega,t)}, \quad (7)$$

where the parameters $\Delta = \omega_0 - m\omega$, $\Omega = \sqrt{\Omega_R^2 + \Delta^2}$, and the Rabi frequency

$$\Omega_B = 2|\mathbf{E}\mathbf{d}_{ab}|mJ_m(\kappa)/\kappa\hbar \tag{8}$$

are written in the vicinity of m-th resonance. Since we consider the strong coupling regime, the driving field strength \mathbf{E} is assumed to be sufficiently strong, $\Omega_R \tau \gg 1$, to neglect impact of the transition natural linewidth \hbar/τ . It should be emphasized that the Rabi frequency in systems with broken inversion symmetry (8) shows non-monotonic dependence on the driving field strength and even can turn zero at those values of \mathbf{E} which correspond to roots of the Bessel function $J_m(\kappa)$.

It is well known that in symmetrical two-level systems the Rabi effect manifests itself in the power spectrum of the scattered light by peaks centered at the incident light frequency ω and at the displaced frequencies $\omega \pm \Omega$ (Mollow triplet, [17]). In order to reveal peculiarities of the scattered light spectrum induced by the symmetry violation, it will suffice to consider the process in the framework of classical electrodynamics. It allows analyzing electronic subsystem, in respect to irradiation of electromagnetic waves, as a classical dipole with the oscillating dipole moment $\mathbf{d}(t) = \langle \psi | \hat{\mathbf{d}} | \psi \rangle$. For definiteness, we identify initial time t=0 as that corresponding to electronic system being in the excited state, i.e., $C_a(0)=1$ and $C_b(0)=0$. Then, substituting wave function $|\psi\rangle$ with coefficients (6)–(7) into expression for the dipole moment and omitting the time-independent terms, we arrive at the expression

$$\mathbf{d}(t) = (\mathbf{d}_{aa} - \mathbf{d}_{bb}) \frac{\Omega_R^2}{4\Omega^2} e^{i\Omega t} - \mathbf{d}_{ab} \frac{\Omega_R}{2\Omega}$$

$$\times \sum_{n = -\infty}^{\infty} J_{m-n}(\kappa) e^{in\omega t} \left[\frac{\Delta}{\Omega} + \frac{1}{2} \left(1 - \frac{\Delta}{\Omega} \right) e^{-i\Omega t} - \frac{1}{2} \left(1 + \frac{\Delta}{\Omega} \right) e^{i\Omega t} \right] + \text{c.c.}$$
(9)

for the dipole moment in the vicinity of m-th resonance. As follows from Eq. (9), the radiation spectrum consists of a singlet at the frequency Ω , and an infinite sequence of triplets with the frequencies $n\omega$, $n\omega \pm \Omega$ (see Fig. 1). Note that amplitudes of harmonics of the triplets rapidly

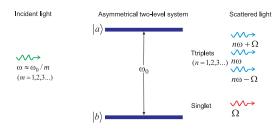


FIG. 1: Schematics of the light scattering in a two-level system with broken inversion symmetry in the vicinity of one of the possible resonances $\omega = \omega_0/m$.

decrease with increasing n or m, while the singlet Ω amplitude depends on neither n nor m. It should be noted also that the radiation of the dipole (9) in the vicinity of each resonance is characterized by its own Rabi frequency (8) decreasing with the resonance number m increase. In systems with inversion symmetry diagonal elements of the dipole moment are identical, $\mathbf{d}_{aa} = \mathbf{d}_{bb}$. As a result, higher resonances (m > 1), higher triplets (n > 1), and the singlet vanish. In that case, coefficients (6)–(7) and expression for the dipole moment (9) coincide with the solution of the problem presented in Ref. [2].

Further we confine consideration to systems with a weak violation of the inversion symmetry, when the condition $|\kappa| \ll 1$ holds true. In such systems the asymmetry effect is expected to be most pronounced in the vicinity

of the first resonance m=1 ($\omega \approx \omega_0$). If then we restrict ourselves to the most interesting case of resonant driving field, when $\Delta=0$ and $\Omega=\Omega_R$, we reduce the dipole moment (9) to the expression

$$\mathbf{d}(t) = \frac{\mathbf{d}_{aa} - \mathbf{d}_{bb}}{2} \cos(\Omega_R t) - \mathbf{d}_{ab} \sin(\omega_0 t) \sin(\Omega_R t), \quad (10)$$

where Rabi frequency (8) takes its conventional form $\Omega_R = |\mathbf{Ed}_{ab}|/\hbar$. In typical quantum systems the Rabi frequency is usually much less then the driving field frequency $\omega = \omega_0$. Therefore, in addition to the high-frequency harmonics $\omega_0 \pm \Omega_R$ (first term in the right-hand part of Eq. (10)), violation of the inversion symmetry leads to the irradiation of low-frequency electromagnetic waves at Rabi frequency (second term in the right-hand part of Eq. (10)) with the time-averaged radiation intensity

$$I_R = \frac{|\mathbf{d}_{aa} - \mathbf{d}_{bb}|^2}{12c^3} \Omega_R^4. \tag{11}$$

The quantity $|\mathbf{d}_{aa} - \mathbf{d}_{bb}|$ is further referred to as effective dipole moment. Note that the frequency of the scattered radiation Ω_R depends only on the driving light strength \mathbf{E} and does not depend on both the characteristic frequency of the scattering system ω_0 and the frequency of incident light ω .

The simplest quantum system devoid of the inversion center is a Rydberg hydrogen atom in the ground state imposed to a homogeneous static electric field \mathcal{E} . Using well-known expressions for wave functions and energy spectrum of the atom, we find that the Rabi frequency in this case is expressed in terms of the Bohr radius $a_B =$ $\hbar^2/m_e e^2$ by $\Omega_R = 4(2/3)^5 e a_B E/\hbar$. Correspondingly, for the electric field ${\mathcal E}$ much less than the intra-atomic electric field e/a_B^2 , the intensity of radiation at the Rabi frequency is determined by Eq. (11) with the effective dipole moment given by $|\mathbf{d}_{aa} - \mathbf{d}_{bb}| = (1/8)(4/3)^{11} a_B^3 \mathcal{E}$. This expression for the effective dipole moment is applicable not only to hydrogen atom but also can be used for estimating parameters of the emission at the Rabi frequency in arbitrary quantum systems with broken inversion symmetry. For that aim, the Bohr radius a_B should be replaced by the characteristic linear extension of the system. Therefore the radiation intensity (11) rises fast with the increase of the system size. In that connection, confined semiconductor nanostructures with discrete energy spectrum and linear extension multiply exceeding the atomic size, quantum dots (QDs) [4], can serve as prospective systems for the effect observation.

In quantum dots, driving electromagnetic field transfers electrons from valence band into conduction band; what is why in QDs ground state $|a\rangle$ corresponds to the absence of free carriers while first excited state $|b\rangle$ is the state with electron in the conduction band and hole in the valence band. In that case, $\hbar\omega_0$ is approximately equal to the semiconductor bandgap, and the Rabi frequency

is determined by the standard expression $\Omega_R = |\mathbf{Ed}_{cv}|/\hbar$ with the dipole matrix element \mathbf{d}_{cv} corresponding to interband transitions. Among a variety of different types of QDs, nitride-based confined structures seem to be most promising for the effect observation. Indeed, whereas usual semiconductor III-V compounds have a cubic (zincblende) crystalline structure, GaN and similar III-group nitride alloys have a hexagonal (wurtzite) structure. For consistent set of parameters of III-nitrides AlN, GaN, and InN see Ref. [18]. As a consequence of giant piezoelectric effect inherent in hexagonal crystals, QDs based on structures AlN/GaN and InN/GaN have a strong builtin strain-induced electric field with strength \mathcal{E} of several MV/cm [19, 20]. Due to the strong electric field, conduction-band electrons and valence-band holes in the QDs get spatially separated [21, 22], and the effective dipole moment of a III-nitride QD is given by simple relation $|\mathbf{d}_{aa} - \mathbf{d}_{bb}| \sim eh$, where h is the QD height. Then, for typical h of several nanometers, the effective dipole moment of nitride QDs is estimated as $|\mathbf{d}_{aa} - \mathbf{d}_{bb}| \sim 10 \,\mathrm{D}$, what is tens thousands times as large as the effective dipole moment of hydrogen atom in the same electric field.

Since the Rabi frequency depends on the driving field strength E, the broken inversion symmetry-induced lowfrequency singlet Ω_R in the dipole emission spectrum can be used for the tunable generation of electromagnetic waves at Rabi frequency with intensity (11). This problem is especially challenging for frequency ranges where traditional methods either fail or inefficient, such as terahertz domain. Since this domain lies between radio and optical frequency ranges, neither optical nor microwave techniques are directly applicable for generating THz waves. Therefore, a search for effective THz radiation sources is one of most excited fields of modern applied physics [23, 24, 25]. One of the latest trends to fill the THz gap is using nanostructures as THz emitters and detectors. The quantum cascade THz transitions in QD systems [26, 27] and different electron mechanisms of THz emission from carbon nanotubes [28, 29, 30] have been proposed and are actively studying. Thus, the proposed mechanism of THz emission fits well the current tendencies in nanophotonics.

Parameters of the THz emission from III-nitride QDs can be evaluated in the following way. Using the estimate $d_{cv} \sim 10\,\mathrm{D}$ for the QD interband dipole moment [18], we obtain that the Rabi frequency turns out to be lying in the THz range at relatively weak strength of the driving field, $E \sim 10^5\,\mathrm{V/cm}$. Then, substituting the previously obtained value of the effective dipole moment $|\mathbf{d}_{aa} - \mathbf{d}_{bb}| \sim 10\,\mathrm{D}$ into Eq. (11), we arrive at the intensity per single QD $I_R \sim 10^{-4}\,\mathrm{eV/s}$ in the THz range. This estimate multiples as N^2 for array of N identical QDs with the lateral extension less than the Rabi wavelength $\lambda_R = 2\pi c/\Omega_R$. In such an array, all QDs emit waves in phase. The terahertz-range wavelength

 $\lambda_R \sim 10^{-2}$ cm restricts the array lateral size. Taking into account that the typical density of nitride QDs is $\sim 10^{11}~{\rm cm^{-2}}$, we can estimate the number of QDs in such an array by $N \sim 10^7-10^8$. Therefore, the THz emission power from the submillimeter-sized QD array may approach the micro-Watt level. Certainly, reducing impact of inhomogeneous broadening is beyond of the estimate and will be considered elsewhere. To conclude, the presented upper estimate of the radiation output allows proposing the broken inversion symmetry-induced mechanism of radiation for the development of novel-type THz emitters based on QDs avoid inversion symmetry. Obviously, parametric amplification of THz radiation in arrays of III-nitride QDs is also possible and can be applied in THz detecting.

Once more type of two-level quantum systems where the discussing effect can be observed is the superconducting quantum circuits [6] formed by Josephson qubits in microstrip resonators. Away from the charge degeneracy point, the qubit symmetry is broken and the Hamiltonian of the system (see Eq. (16) in Ref. [6]) takes the form analogous to that used in our analysis. At that, the resonant transition frequency amounts to $\sim 10 \, \mathrm{GHz}$ while the Rabi frequency lies in the range $\sim 100\,\mathrm{MHz}$. Intensity of low-frequency line in the spectrum of Rabi oscillations can be controlled by the changing of dc gate voltage. Chiral nanostructures, such as sculptured thin films [31], semiconductor nanohelices [32] and carbon nanotubes, should also be noted as prospective systems for observation of the effect, since chirality breaks the inversion symmetry.

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